

IN THE CLAIMS:

Please cancel claims 7-19 without prejudice or disclaimer.

1. (Original) A semiconductor device, comprising:
 - a semiconductor layer;
 - a gate insulator layer formed on the semiconductor layer; and
 - a gate electrode formed on the gate insulator layer, wherein the atomic ratio of oxygen atoms included in the gate insulator layer is 5 atm. % or below.
2. (Original) A semiconductor device, comprising:
 - a semiconductor layer;
 - a gate insulator layer formed on the semiconductor layer and having an interface reaction layer; and
 - a gate electrode formed on the gate insulator layer, wherein the atomic ratio of oxygen atoms included in the gate insulator layer is approximately 5 atm. % or below.
3. (Original) The semiconductor device according to Claim 1 or 2, wherein the gate insulator layer is a silicon nitride layer.
4. (Original) The semiconductor device according to Claim 3, wherein the silicon nitride layer is formed by the reaction of a nitrogen species activated by plasma excitation directly with the semiconductor layer.
5. (Original) The semiconductor device according to any one of Claims 1, 2, or 4, wherein the gate electrode includes a tantalum nitride layer.
6. (Original) The semiconductor device according to Claim 5, wherein the tantalum nitride layer is formed by sputtering.

Claims 7-19 (Cancelled).

20. (New) A semiconductor device, comprising:
a semiconductor layer;
a gate insulator layer formed on the semiconductor layer; and
a gate electrode formed on the gate insulator layer, wherein the atomic ratio of oxygen atoms included in the entire gate insulator layer is 5 atm. % or below.

21. (New) A semiconductor device, comprising:
a semiconductor layer;
a gate insulator layer formed on the semiconductor layer, wherein the gate insulator layer does not include an interface reaction layer including oxygen at an interface with the gate electrode; and
a gate electrode formed on the gate insulator layer, wherein the atomic ratio of oxygen atoms included in the gate insulator layer is 5 atm. % or below.